Recent advances in Schottky barrier concepts

Materials Science and Engineering Reports
35, 1-138
DOI: 10.1016/s0927-796x(01)00037-7

Citation Report

#	Article	IF	Citations
1	Scanning spreading resistance microscopy current transport studies on doped IIIâ€“V semiconductors. Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena, 2002, 20, 1682.	1.6	36
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1005	Voltammetric Measurement of Rates and Energetics for Surface Methoxylation of Si(100) in Methanol with Dissolved Electron Acceptors Using Si Ultramicroelectrodes. Analytical Chemistry, 0, , .	3.2	0
1010	Harnessing the hydrogen evolution reaction (HER) through the electrical mobility of an embossed Ag(<scp>i</scp>)-molecular cage and a Cu(<scp>ii</scp>)-coordination polymer. Dalton Transactions, 2023, 52, 8850-8856.	1.6	6
1031	Modeling forward characteristics of high temperature capable Schottky diodes â€“ High-accuracy optimization methods â€“. , 2023, , .		0